Docket Number: 011765-0304367 Client Reference: AF/JG/P9094US



PATENT APPLICAT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of

FLORIN UDREA

Group Art Unit: 2814

Application No.: 10/602,065

Examiner: PHAM, Hoai V.

Filed: June 24, 2003

Confirmation No.: 1160

For: LATERAL SEMICONDUCTOR DEVICE

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR 1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom. Applicants respectfully request the Examiner return an initialed copy of the enclosed Form PTO-1449 to Applicants with the next Office communication to indicate that the reference(s) has been considered, per MPEP § 609.

This Information Disclosure Statement is being filed more than three months after the U.S. filing date and after the mailing date of the Notice of Allowance, but before payment of the Issue Fee. Please charge Deposit Account 03-3975, under order number 011765-0304367, in the amount of \$180.00 in payment of the fee under 37 CFR 1.17(i)(p). Please credit or debit Deposit Account 03-3975 as needed to ensure consideration of the disclosed information.

These references are being cited with respect to an International Search Report which was issued for International Application No. PCT/GB 03/02635. Applicant is submitting U.S. Patent No. 2002/0096708 as the U.S. equivalent of EP 1 213 768.

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Respectfully Submitted,

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	TR Udrea, F., et al., "Lateral Insulated Gate Bipolar Transistor (LIGBT) Structure Based on Partial Isolation SOI Technology," 8 May 1997, pgs. 907-909.														
	UR	Chen, X.B., et al., "Lateral High-Voltage Devices Using an Optimized Variational Lateral Doping," Int. J. Electronics, 1996, Vol. 80, No. 3, pgs. 449-459.													
	VR	Amberetu, M., et al., "150-V Class Superjunction Power LDMOS Transistor Switch on SOI, 4 June 2002, pgs. 101-104.													
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